Characteristics T1610T-8I

1 Characteristics

Table 2. Absolute maximum rating ($T_j = 25$ °C, unless otherwise specified)

Symbol	Parameter				Unit	
	On-state rms current (full sine wave)		T _c = 108 °C	16	Α	
I _{T(RMS)}			T _c = 119 °C	12		
1.	Non repetitive surge peak on-state current (full	F = 50 Hz	t = 20 ms	120	Λ.	
I _{TSM}	cycle, T _j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	126	Α	
l ² t	I^2 t Value for fusing $t_p = 10 \text{ ms}$				A ² s	
V _{DRM} ,	Penetitive peak off state valtage gate apen			600	V	
V_{RRM}	Repetitive peak off-state voltage, gate open	T _j = 125 °C	800			
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state voltage	T _j = 25 °C	900	V		
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ F = 100 Hz			100	A/µs	
I _{GM}	Peak gate current $t_p = 20 \mu s$			4	Α	
P _{G(AV)}	Average gate power dissipation			1	W	
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			-40 to +150 -40 to +150	°C	
TL	Lead temperature for soldering during 10 s (at 4 mm from case for TO220AB-ins.)			260	°C	
V _{ins} (rms)	Insulation rms voltage, 1 minute, TO220AB ceramic insulated			2500	V	

T1610T-8I Characteristics

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions		Quadrant		Value	Unit
ı (1)	$I_{GT}^{(1)}$ $V_D = 12 \text{ V}, R_L = 30 \Omega$		I - II - III	MIN.	0.5	mA
'GT ` ′			1 - 11 - 111	MAX.	10	mA
V _{GT}	VD = 12 V, RL = 30 Ω		All	MAX.	1.3	V
V_{GD}	V_D = 800 V, R_L = 3.3 k Ω , T_j = 125 °C		All	MIN.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA			MAX.	25	mA
	1 121		I - III	MAX.	20	mA
IL	$I_{G} = 1.2 I_{GT}$	II	30			
dV/dt (1)	V _D = 67% x 800 V gate open	T _j = 125 °C		MIN.	100	V/µs
u v/ut v /	V _D = 67% x 600 V gate open	T _j = 150 °C		IVIIIN.	50	
	(dV/dt)c = 0.1 V/μs	T _j = 125 °C			9	
(dl/dt)c (1)	(dV/dt)c = 10 V/μs	T _j = 125 °C		MIN.	3	A/ms
(ui/ut)e v	(dV/dt)c = 0.1 V/μs	T _j = 150 °C		IVIIIN.	5.4	
	(dV/dt)c = 10 V/μs	T _j = 150 °C			1.8	
t _{GT}	gate controlled turn on time I_{TM} = 13 A, V_D = 400 V, I_G = 100 mA, dI_G /dt = 100 mA/ μ s, R_L = 30 Ω		I - II - III	TYP.	2	μs

^{1.} For both polarities of A2 referenced to A1

Table 4. Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM} ⁽¹⁾	$I_{TM} = 22.6 \text{ A}, t_p = 380 \mu\text{s}$	T _j = 25 °C	MAX.	1.55	V
V _{to} (1)	Threshold voltage	T _j = 150 °C	MAX.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	MAX.	30	mΩ
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM} = 800 V	T _j = 25 °C	MAX.	5	μΑ
		T _j = 125 °C		1	mA
	V _{DRM} = V _{RRM} = 600 V	T _j = 150 °C		3.6	

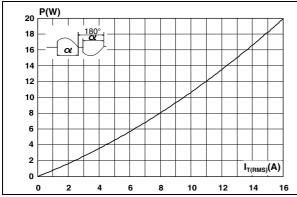
^{1.} for both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.1	°C/W
R _{th(j-a)}	Junction to ambient	60	°C/W

Characteristics T1610T-8I

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case on-state rms current (full cycle) temperature (full cycle)



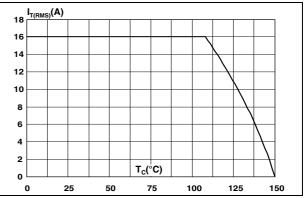
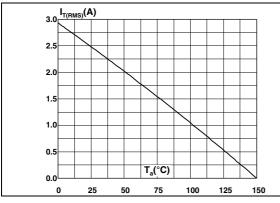


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration



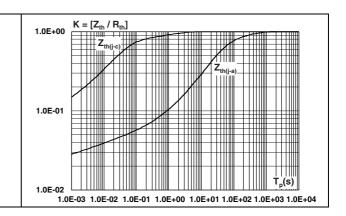
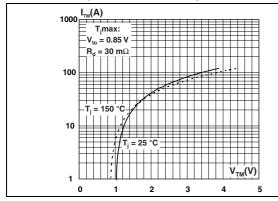
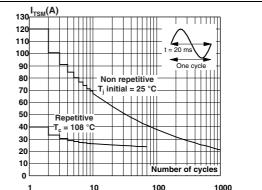


Figure 5. On-state characteristics (maximum values)

Figure 6. Surge peak on-state current versus number of cycles





T1610T-8I Characteristics

Figure 7. Non repetitive surge peak on-state Figure 8. Relative variation of gate trigger current and corresponding values of I²t Relative variation of gate trigger current versus junction temperature (typical values)

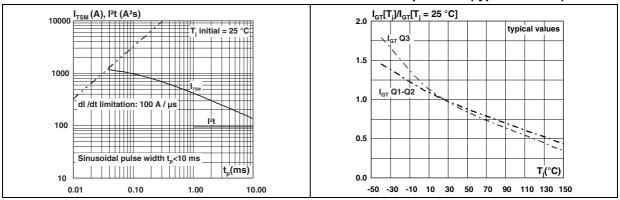


Figure 9. Relative variation of gate trigger voltage versus junction temperature (typical values)

Figure 10. Relative variation of holding current and latching current versus junction temperature

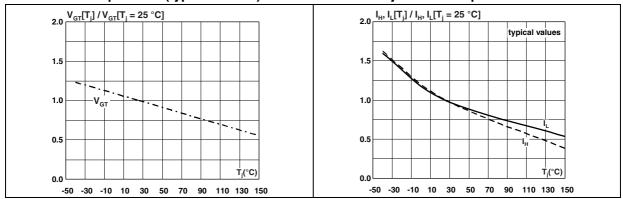
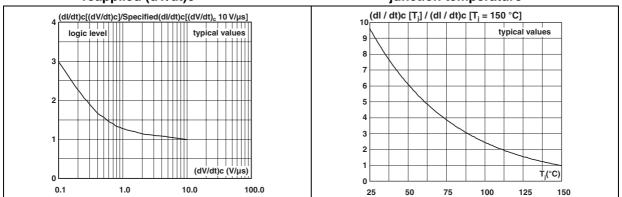


Figure 11. Relative variation of critical rate of decrease of current (dl/dt)c versus reapplied (dV/dt)c

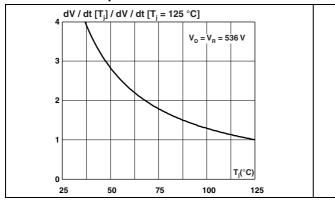
igure 12. Relative variation of critical rate of decrease of current (dl/dt)c versus junction temperature



Characteristics T1610T-8I

Figure 13. Relative variation of static dV/dt immunity versus junction temperature

Figure 14. Relative variation of static dV/dt immunity versus junction temperature



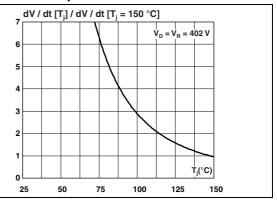
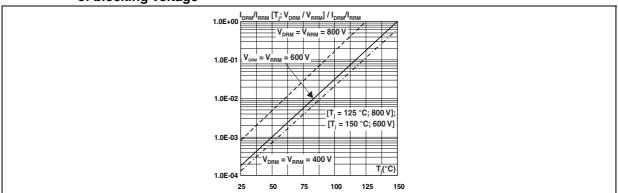


Figure 15. Relative variation of leakage current versus junction temperature for different values of blocking voltage



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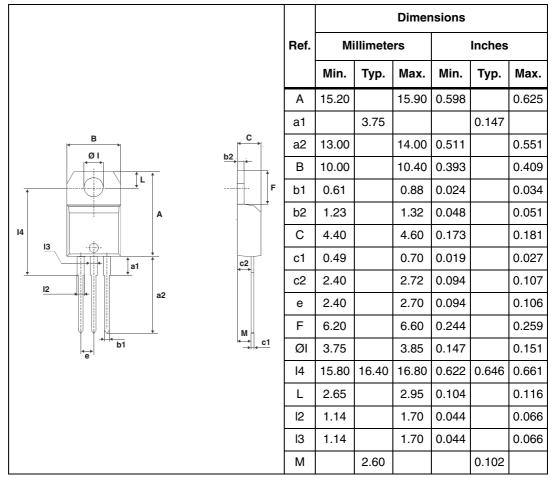
T1610T-8I Package information

2 Package information

- Epoxy meets UL94, V0
- Recommended torque value: 0.4 to 0.6 N·m

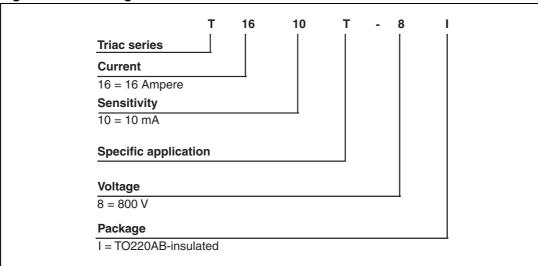
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Table 6. TO-220AB insulated dimensions



3 Ordering information scheme

Figure 16. Ordering information scheme



4 Ordering information

 Table 7.
 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1610T-8I	T1610T-8I	TO-220AB insulated	2.3	50	Tube

5 Revision history

Table 8. Document revision history

Date	Revision	Changes
08-Aug-2011	1	First issue.
20-Jan-2012	2	Corrected subscripting error in <i>Table 3</i> .
25-Apr-2012	3	Updated UL certification.

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